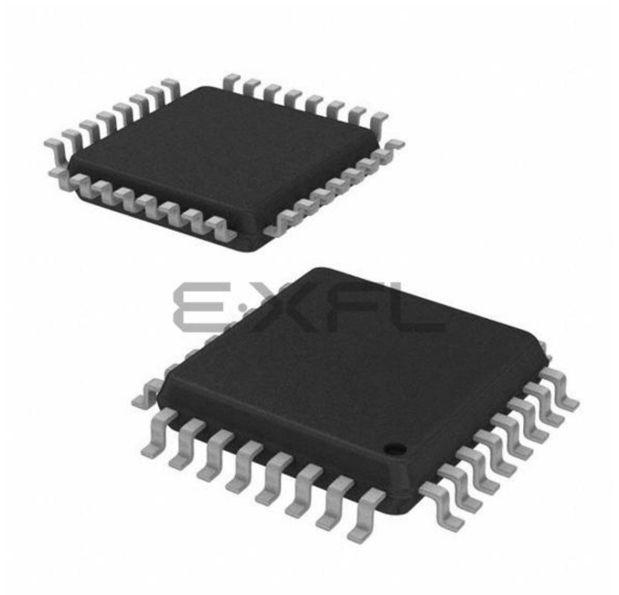

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	40MHz
Connectivity	I²C, SPI, UART/USART
Peripherals	LVD, PWM, WDT
Number of I/O	28
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	256 x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 16x12b; D/A 2x6b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mke02z16vlc4

- Timers
  - One 6-channel FlexTimer/PWM (FTM)
  - Two 2-channel FlexTimer/PWM (FTM)
  - One 2-channel periodic interrupt timer (PIT)
  - One real-time clock (RTC)
- Communication interfaces
  - Two SPI modules (SPI)
  - Up to three UART modules (UART)
  - One I2C module (I2C)
- Package options
  - 64-pin QFP/LQFP
  - 44-pin LQFP
  - 32-pin LQFP
  - 32-pin QFN

Field	Description	Values
T	Temperature range (°C)	• V = –40 to 105
PP	Package identifier	• LC = 32 LQFP (7 mm x 7 mm) • FM = 32 QFN (5 mm x 5 mm) • LD = 44 LQFP (10 mm x 10 mm) • QH = 64 QFP (14 mm x 14 mm) • LH = 64 LQFP (10 mm x 10 mm)
CC	Maximum CPU frequency (MHz)	• 4 = 40 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

2.4 Example

This is an example part number:

MKE02Z64VQH4

3 Parameter classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding, the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 1. Parameter classifications

P	Those parameters are guaranteed during production testing on each individual device.
C	Those parameters are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters are derived mainly from simulations.

NOTE

The classification is shown in the column labeled “C” in the parameter tables where appropriate.

4 Ratings

4.1 Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.2 Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

4.3 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	–6000	+6000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	–500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 125°C	–100	+100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78D, *IC Latch-up Test*.
    - Test was performed at 125 °C case temperature (Class II).
    - I/O pins pass ±100 mA I-test with I_{DD} current limit at 800 mA.
    - I/O pins pass +60/-100 mA I-test with I_{DD} current limit at 1000 mA.
    - Supply groups pass 1.5 V_{ccmax}.
    - $\overline{\text{RESET}}$ pin was only tested with negative I-test due to product conditioning requirement.

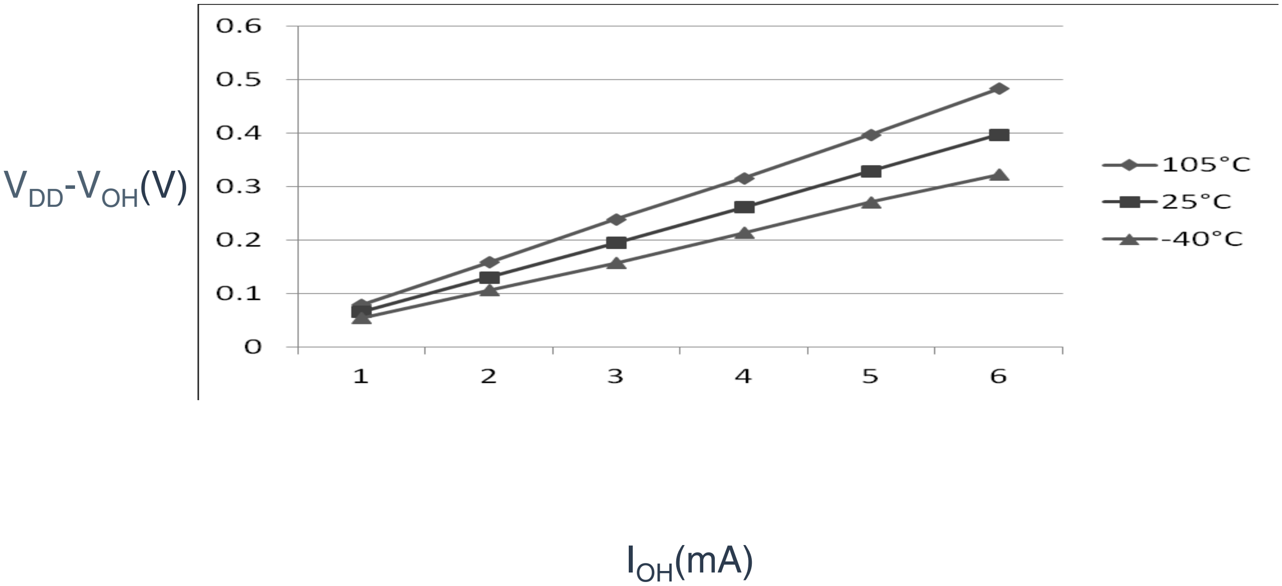


Figure 1. Typical V_{DD}-V_{OH} Vs. I_{OH} (standard drive strength) (V_{DD} = 5 V)

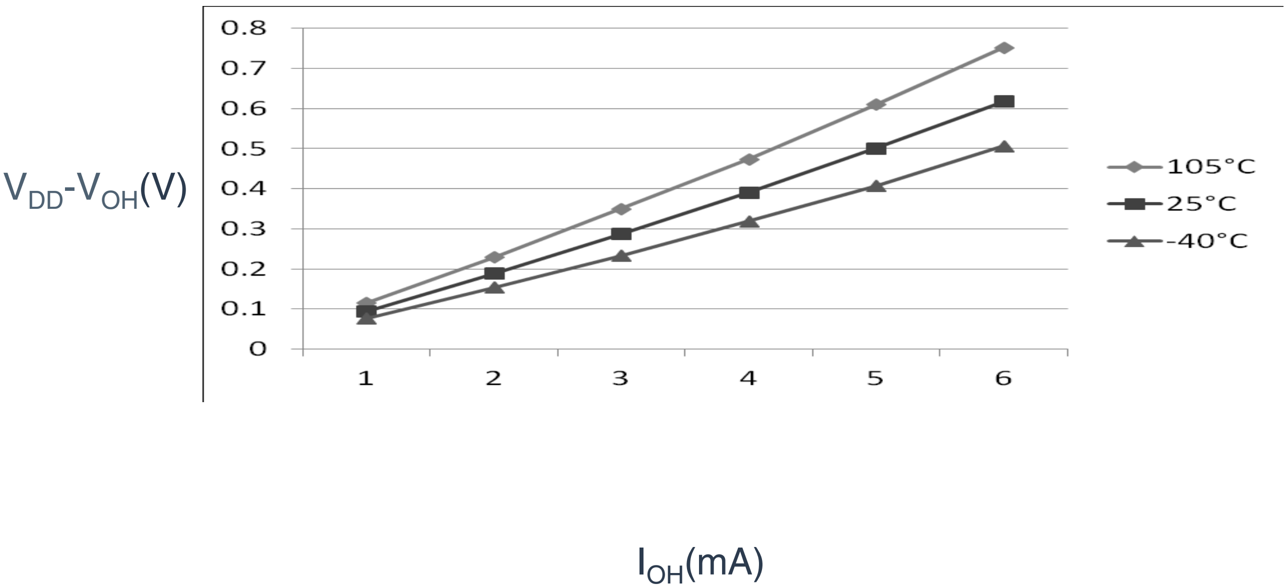


Figure 2. Typical V_{DD}-V_{OH} Vs. I_{OH} (standard drive strength) (V_{DD} = 3 V)

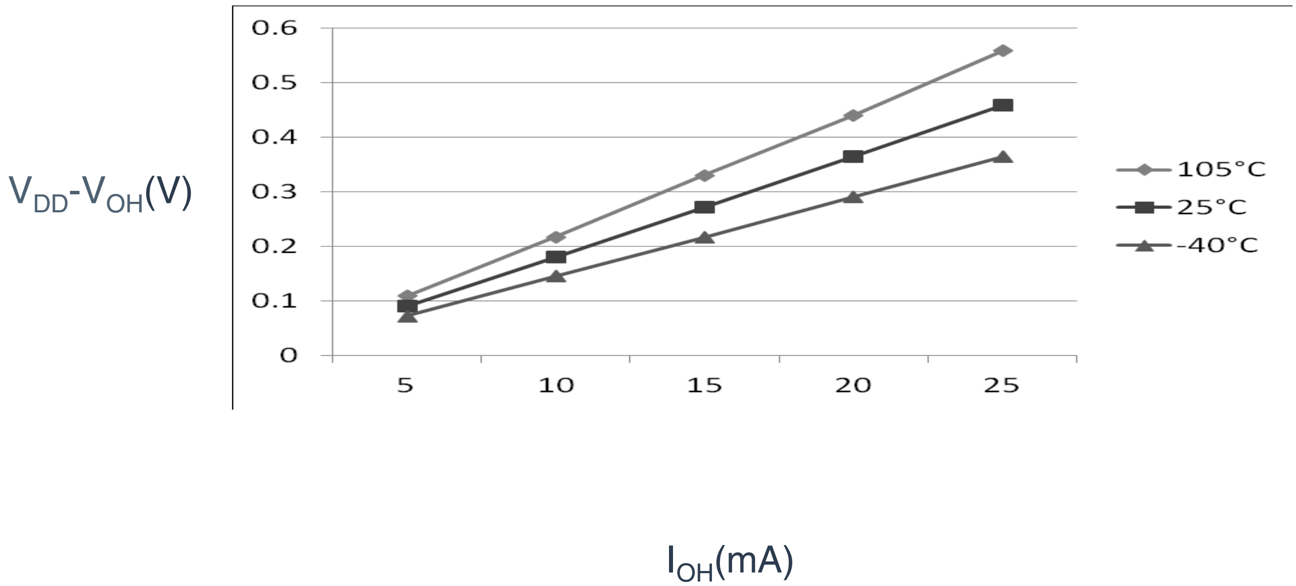


Figure 3. Typical V_{DD}-V_{OH} Vs. I_{OH} (high drive strength) (V_{DD} = 5 V)

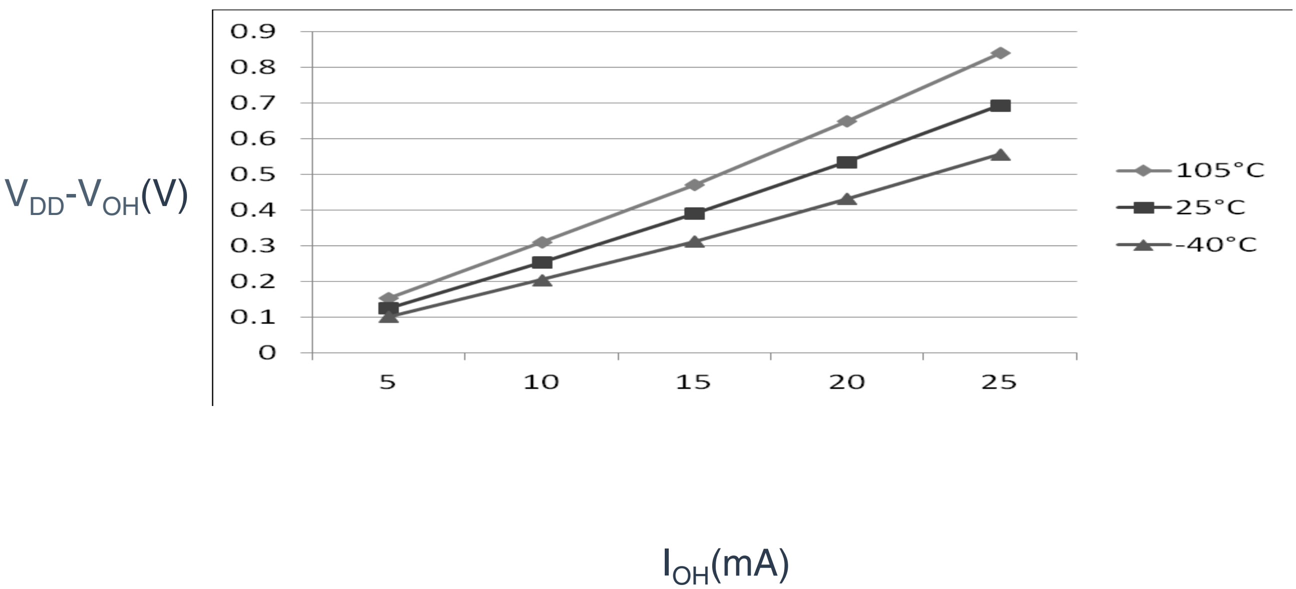


Figure 4. Typical V_{DD}-V_{OH} Vs. I_{OH} (high drive strength) (V_{DD} = 3 V)

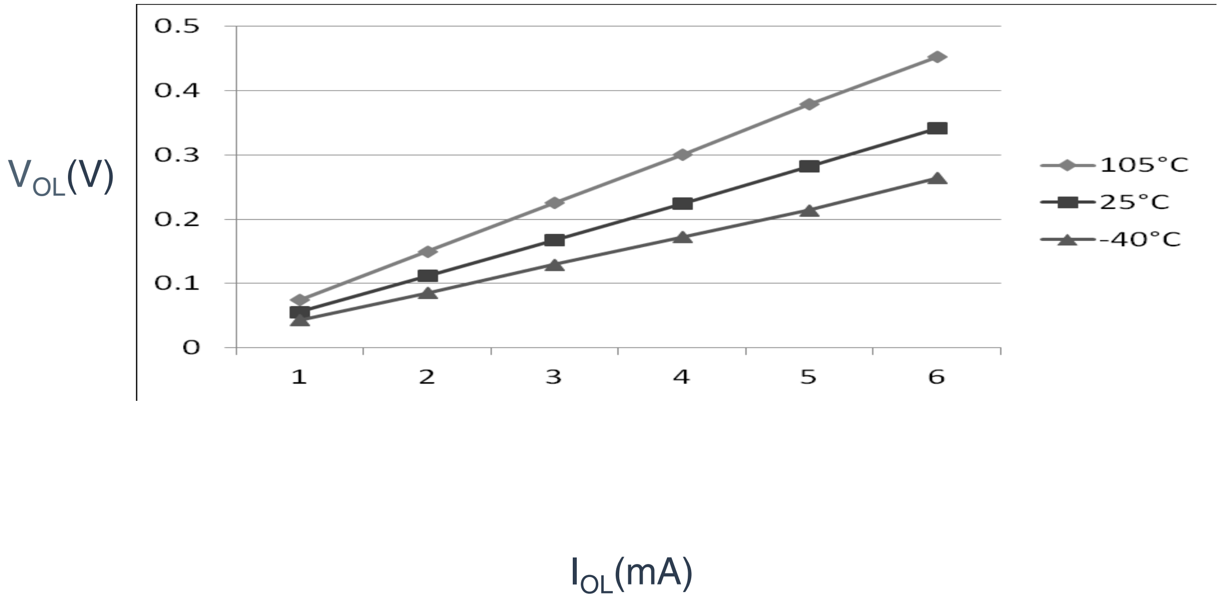


Figure 5. Typical V_{OL} Vs. I_{OL} (standard drive strength) (V_{DD} = 5 V)

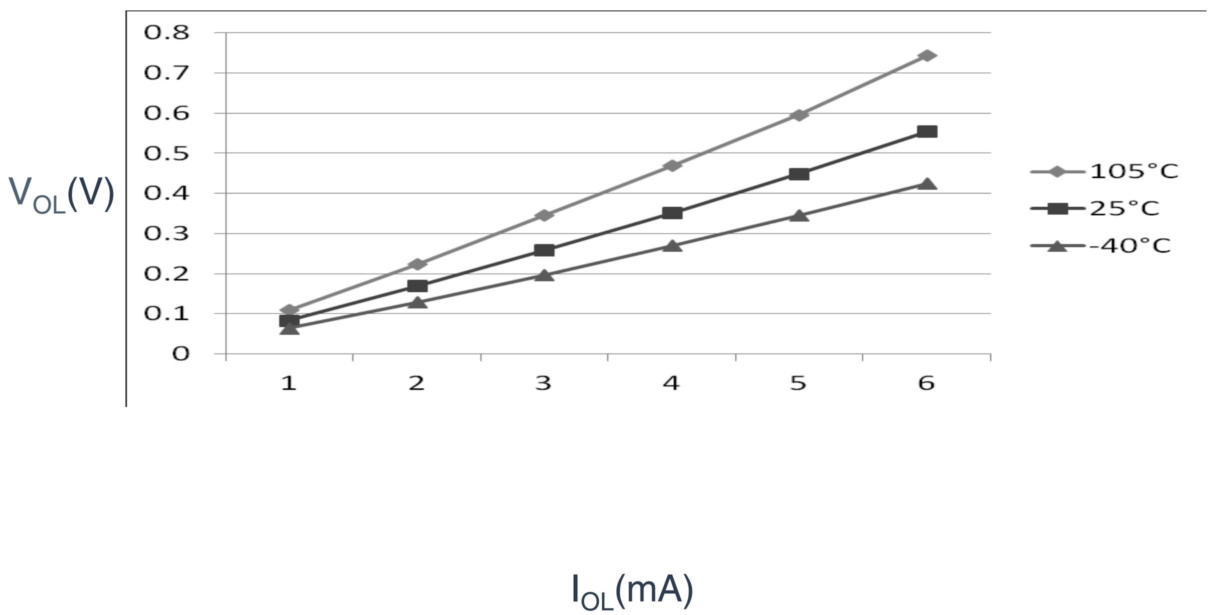


Figure 6. Typical V_{OL} Vs. I_{OL} (standard drive strength) (V_{DD} = 3 V)

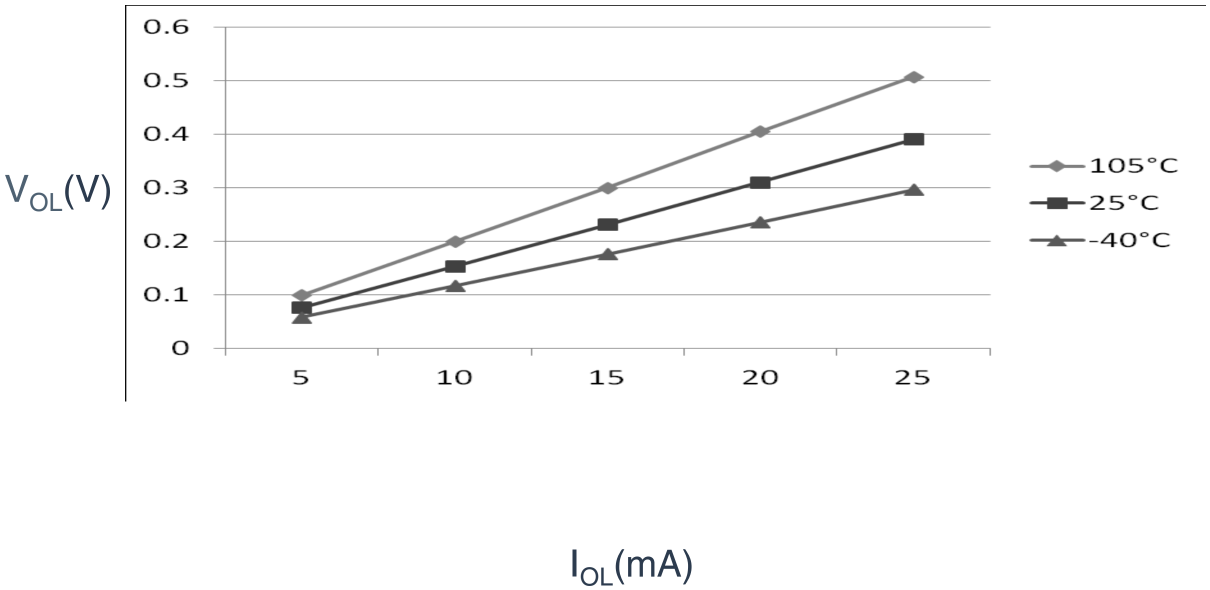


Figure 7. Typical V_{OL} Vs. I_{OL} (high drive strength) (V_{DD} = 5 V)

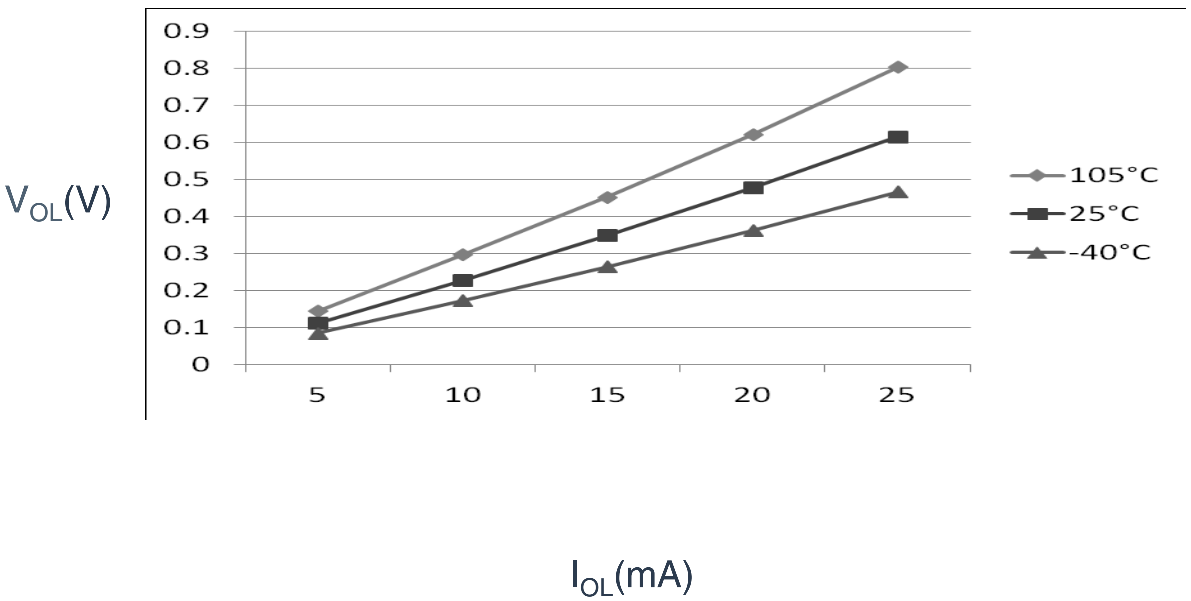


Figure 8. Typical V_{OL} Vs. I_{OL} (high drive strength) (V_{DD} = 3 V)

Table 7. Control timing (continued)

Num	C	Rating		Symbol	Min	Typical[1]	Max	Unit
7	D	Keyboard interrupt pulse width	Asynchronous path[2]	t_{ILIH}	100	—	—	ns
	D		Synchronous path	t_{IHIL}	$1.5 \times t_{cyc}$	—	—	ns
8	C	Port rise and fall time - Normal drive strength (load = 50 pF)[4]	—	t_{Rise}	—	10.2	—	ns
	C			t_{Fall}	—	9.5	—	ns
	C	Port rise and fall time - high drive strength (load = 50 pF)[4]	—	t_{Rise}	—	5.4	—	ns
	C			t_{Fall}	—	4.6	—	ns

1. Typical values are based on characterization data at V_{DD} = 5.0 V, 25 °C unless otherwise stated.
2. This is the shortest pulse that is guaranteed to be recognized as a $\overline{\text{RESET}}$ pin request.
3. This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized.
4. Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range -40 °C to 105 °C.

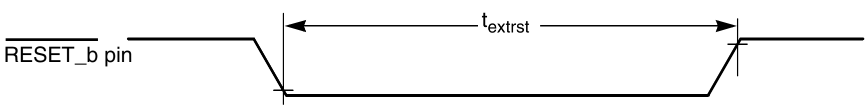


Figure 9. Reset timing

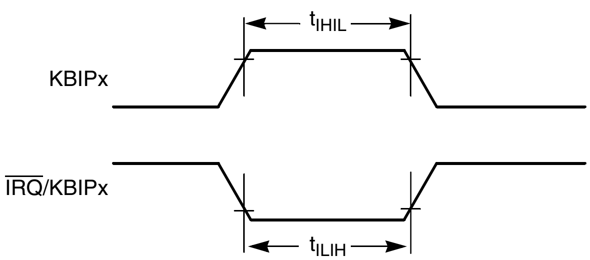


Figure 10. KBIPx timing

5.2.2 FTM module timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the timer counter. These synchronizers operate from the current bus rate clock.

Table 8. FTM input timing

C	Function	Symbol	Min	Max	Unit
D	External clock frequency	f_{TCLK}	0	$f_{Bus}/4$	Hz
D	External clock period	t_{TCLK}	4	—	t_{cyc}

Table continues on the next page...

Table 8. FTM input timing (continued)

C	Function	Symbol	Min	Max	Unit
D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
D	External clock low time	t_{clkl}	1.5	—	t_{cyc}
D	Input capture pulse width	t_{ICPW}	1.5	—	t_{cyc}

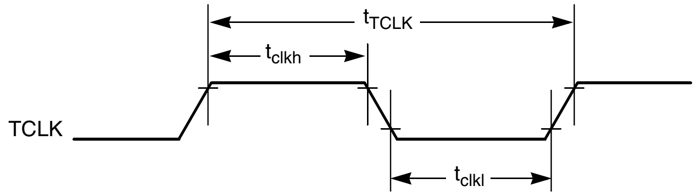


Figure 11. Timer external clock

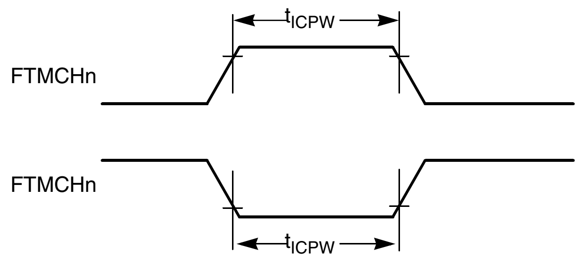


Figure 12. Timer input capture pulse

5.3 Thermal specifications

5.3.1 Thermal operating requirements

Table 9. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
T_J	Die junction temperature	–40	125	°C	
T_A	Ambient temperature	–40	105	°C	1

1. Maximum T_A can be exceeded only if the user ensures that T_J does not exceed maximum T_J. The simplest method to determine T_J is: $T_J = T_A + \theta_{JA}$ x chip power dissipation

Where:

T_A = Ambient temperature, °C

θ_{JA} = Package thermal resistance, junction-to-ambient, °C/W

$P_D = P_{int} + P_{I/O}$

$P_{int} = I_{DD} \times V_{DD}$, Watts - chip internal power

$P_{I/O}$ = Power dissipation on input and output pins - user determined

For most applications, $P_{I/O} << P_{int}$ and can be neglected. An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is:

$P_D = K \div (T_J + 273\ °C)$

Solving the equations above for K gives:

$K = P_D \times (T_A + 273\ °C) + \theta_{JA} \times (P_D)^2$

where K is a constant pertaining to the particular part. K can be determined by measuring P_D (at equilibrium) for an known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving the above equations iteratively for any value of T_A.

6 Peripheral operating requirements and behaviors

6.1 Core modules

6.1.1 SWD electricals

Table 11. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	2.7	5.5	V
J1	SWD_CLK frequency of operation • Serial wire debug	0	20	MHz
J2	SWD_CLK cycle period	1/J1	—	ns
J3	SWD_CLK clock pulse width • Serial wire debug	20	—	ns
J4	SWD_CLK rise and fall times	—	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	—	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	3	—	ns

Table continues on the next page...

Table 13. Flash and EEPROM characteristics (continued)

C	Characteristic	Symbol	Min[1]	Typical[2]	Max[3]	Unit[4]
D	NVM Bus frequency	f_{NVMBUS}	1	—	25	MHz
D	NVM Operating frequency	f_{NVMOP}	0.8	1	1.05	MHz
D	Erase Verify All Blocks	t_{VFYALL}	—	—	17338	t_{cyc}
D	Erase Verify Flash Block	t_{RD1BLK}	—	—	16913	t_{cyc}
D	Erase Verify EEPROM Block	t_{RD1BLK}	—	—	810	t_{cyc}
D	Erase Verify Flash Section	t_{RD1SEC}	—	—	484	t_{cyc}
D	Erase Verify EEPROM Section	$t_{DRD1SEC}$	—	—	555	t_{cyc}
D	Read Once	t_{RDONCE}	—	—	450	t_{cyc}
D	Program Flash (2 word)	t_{PGM2}	0.12	0.12	0.29	ms
D	Program Flash (4 word)	t_{PGM4}	0.20	0.21	0.46	ms
D	Program Once	$t_{PGMONCE}$	0.20	0.21	0.21	ms
D	Program EEPROM (1 Byte)	t_{DPGM1}	0.10	0.10	0.27	ms
D	Program EEPROM (2 Byte)	t_{DPGM2}	0.17	0.18	0.43	ms
D	Program EEPROM (3 Byte)	t_{DPGM3}	0.25	0.26	0.60	ms
D	Program EEPROM (4 Byte)	t_{DPGM4}	0.32	0.33	0.77	ms
D	Erase All Blocks	t_{ERSALL}	96.01	100.78	101.49	ms
D	Erase Flash Block	t_{ERSBLK}	95.98	100.75	101.44	ms
D	Erase Flash Sector	t_{ERSPG}	19.10	20.05	20.08	ms
D	Erase EEPROM Sector	t_{DERSPG}	4.81	5.05	20.57	ms
D	Unsecure Flash	t_{UNSECU}	96.01	100.78	101.48	ms
D	Verify Backdoor Access Key	t_{VFYKEY}	—	—	464	t_{cyc}
D	Set User Margin Level	t_{MLOADU}	—	—	407	t_{cyc}
C	FLASH Program/erase endurance T_L to T_H = -40 °C to 105 °C	n_{FLPE}	10 k	100 k	—	Cycles
C	EEPROM Program/erase endurance TL to TH = -40 °C to 105 °C	n_{FLPE}	50 k	500 k	—	Cycles
C	Data retention at an average junction temperature of T_{Javg} = 85°C after up to 10,000 program/erase cycles	t_{D_ret}	15	100	—	years

1. Minimum times are based on maximum f_{NVMOP} and maximum f_{NVMBUS}
2. Typical times are based on typical f_{NVMOP} and maximum f_{NVMBUS}
3. Maximum times are based on typical f_{NVMOP} and typical f_{NVMBUS} plus aging
4. $t_{cyc} = 1 / f_{NVMBUS}$

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Flash Memory Module section in the reference manual.

6.4 Analog

6.4.1 ADC characteristics

Table 14. 5 V 12-bit ADC operating conditions

Characteristic	Conditions	Symbol	Min	Typ[1]	Max	Unit	Comment
Reference potential	• Low • High	V_{REFL} V_{REFH}	V_{SSA} V_{DDA}	— —	V_{SSA} V_{DDA}	V	—
Supply voltage	Absolute	V_{DDA}	2.7	—	5.5	V	—
	Delta to V_{DD} (V_{DD}-V_{DDA})	ΔV_{DDA}	-100	0	+100	mV	—
Ground voltage	Delta to V_{SS} (V_{SS}-V_{SSA})	ΔV_{SSA}	-100	0	+100	mV	—
Input voltage		V_{ADIN}	V_{REFL}	—	V_{REFH}	V	—
Input capacitance		C_{ADIN}	—	4.5	5.5	pF	—
Input resistance		R_{ADIN}	—	3	5	kΩ	—
Analog source resistance	12-bit mode • f_{ADCK} > 4 MHz • f_{ADCK} < 4 MHz	R_{AS}	— —	— —	2 5	kΩ	External to MCU
	10-bit mode • f_{ADCK} > 4 MHz • f_{ADCK} < 4 MHz		— —	— —	5 10		
	8-bit mode (all valid f_{ADCK})		—	—	10		
ADC conversion clock frequency	High speed (ADLPC=0)	f_{ADCK}	0.4	—	8.0	MHz	—
	Low power (ADLPC=1)		0.4	—	4.0		

1. Typical values assume V_{DDA} = 5.0 V, Temp = 25°C, f_{ADCK}=1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

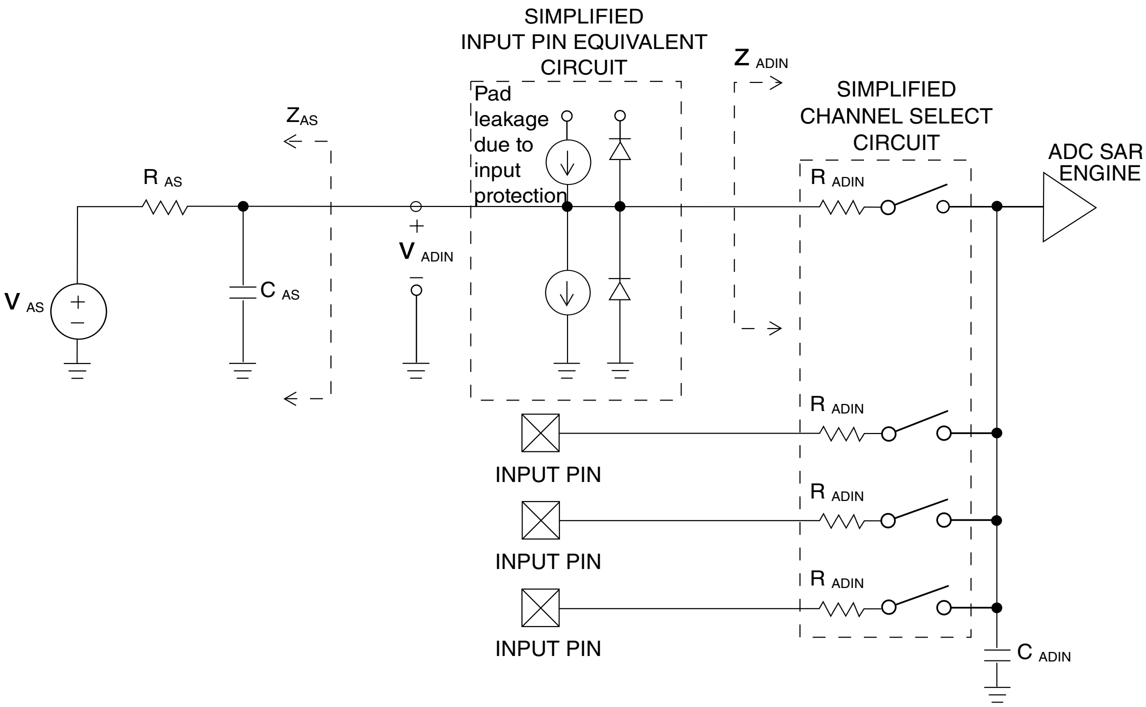


Figure 16. ADC input impedance equivalency diagram

Table 15. 12-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Characteristic	Conditions	C	Symbol	Min	Typ[1]	Max	Unit
Supply current ADLPC = 1 ADLSMP = 1 ADCO = 1		T	I_{DDA}	—	133	—	µA
Supply current ADLPC = 1 ADLSMP = 0 ADCO = 1		T	I_{DDA}	—	218	—	µA
Supply current ADLPC = 0 ADLSMP = 1 ADCO = 1		T	I_{DDA}	—	327	—	µA
Supply current ADLPC = 0 ADLSMP = 0 ADCO = 1		T	I_{DDA}	—	582	990	µA
Supply current	Stop, reset, module off	T	I_{DDA}	—	0.011	1	µA
ADC asynchronous clock source	High speed (ADLPC = 0)	P	f_{ADACK}	2	3.3	5	MHz

Table continues on the next page...

Table 15. 12-bit ADC characteristics (V_{REFH} = V_{DDA}, V_{REFL} = V_{SSA}) (continued)

Characteristic	Conditions	C	Symbol	Min	Typ[1]	Max	Unit
	Low power (ADLPC = 1)			1.25	2	3.3	
Conversion time (including sample time)	Short sample (ADLSMP = 0)	T	t_{ADC}	—	20	—	ADCK cycles
	Long sample (ADLSMP = 1)			—	40	—	
Sample time	Short sample (ADLSMP = 0)	T	t_{ADS}	—	3.5	—	ADCK cycles
	Long sample (ADLSMP = 1)			—	23.5	—	
Total unadjusted Error[2]	12-bit mode[3]	T	E_{TUE}	—	±3.6	—	LSB[4]
	10-bit mode	P		—	±1.5	±2.0	
	8-bit mode	T		—	±0.7	±1.0	
Differential Non-Liniarity	12-bit mode	T	DNL	—	±1.0	—	LSB[4]
	10-bit mode[5]	P		—	±0.25	±0.5	
	8-bit mode[5]	T		—	±0.15	±0.25	
Integral Non-Linearity	12-bit mode[3]	T	INL	—	±1.0	—	LSB[4]
	10-bit mode	T		—	±0.3	±0.5	
	8-bit mode	T		—	±0.15	±0.25	
Zero-scale error[6]	12-bit mode	C	E_{ZS}	—	±2.0	—	LSB[4]
	10-bit mode	P		—	±0.25	±1.0	
	8-bit mode	T		—	±0.65	±1.0	
Full-scale error[7]	12-bit mode	T	E_{FS}	—	±2.5	—	LSB[4]
	10-bit mode	T		—	±0.5	±1.0	
	8-bit mode	T		—	±0.5	±1.0	
Quantization error	≤12 bit modes	D	E_Q	—	—	±0.5	LSB[4]
Input leakage error[8]	all modes	D	E_{IL}	I_{In} * R_{AS}			mV
Temp sensor slope	-40 °C–25 °C	D	m	—	3.266	—	mV/°C
	25 °C–125 °C			—	3.638	—	
Temp sensor voltage	25 °C	D	V_{TEMP25}	—	1.396	—	V

1. Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK}=1.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.
2. Includes quantization
3. This parameter is valid for the temperature range of 25 °C to 50 °C.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. Monotonicity and no-missing-codes guaranteed in 10-bit and 8-bit modes
6. V_{ADIN} = V_{SSA}
7. V_{ADIN} = V_{DDA}
8. I_{In} = leakage current (refer to DC characteristics)

6.4.2 Analog comparator (ACMP) electricals

Table 16. Comparator electrical specifications

C	Characteristic	Symbol	Min	Typical	Max	Unit
D	Supply voltage	V_{DDA}	2.7	—	5.5	V
T	Supply current (Operation mode)	I_{DDA}	—	10	20	µA
D	Analog input voltage	V_{AIN}	V_{SS} - 0.3	—	V_{DDA}	V
P	Analog input offset voltage	V_{AIO}	—	—	40	mV
C	Analog comparator hysteresis (HYST=0)	V_H	—	15	20	mV
C	Analog comparator hysteresis (HYST=1)	V_H	—	20	30	mV
T	Supply current (Off mode)	I_{DDAOFF}	—	60	—	nA
C	Propagation Delay	t_D	—	0.4	1	µs

6.5 Communication interfaces

6.5.1 SPI switching specifications

The serial peripheral interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's reference manual for information about the modified transfer formats used for communicating with slower peripheral devices. All timing is shown with respect to 20% V_{DD} and 80% V_{DD}, unless noted, and 25 pF load on all SPI pins. All timing assumes high-drive strength is enabled for SPI output pins.

Table 17. SPI master mode timing

Num.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	f_{Bus}/2048	f_{Bus}/2	Hz	f_{Bus} is the bus clock
2	t_{SPSCK}	SPSCK period	2 x t_{Bus}	2048 x t_{Bus}	ns	$t_{Bus} = 1/f_{Bus}$
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{Bus} – 30	1024 x t_{Bus}	ns	—
6	t_{SU}	Data setup time (inputs)	8	—	ns	—
7	t_{HI}	Data hold time (inputs)	8	—	ns	—
8	t_v	Data valid (after SPSCK edge)	—	25	ns	—
9	t_{HO}	Data hold time (outputs)	20	—	ns	—
10	t_{RI}	Rise time input	—	t_{Bus} – 25	ns	—

Table continues on the next page...

Table 18. SPI slave mode timing

Num.	Symbol	Description	Min.	Max.	Unit	Comment
1	f_{op}	Frequency of operation	0	$f_{Bus}/4$	Hz	f_{Bus} is the bus clock as defined in Control timing.
2	t_{SPSCK}	SPSCK period	4 x t_{Bus}	—	ns	$t_{Bus} = 1/f_{Bus}$
3	t_{Lead}	Enable lead time	1	—	t_{Bus}	—
4	t_{Lag}	Enable lag time	1	—	t_{Bus}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{Bus} - 30	—	ns	—
6	t_{SU}	Data setup time (inputs)	15	—	ns	—
7	t_{HI}	Data hold time (inputs)	25	—	ns	—
8	t_a	Slave access time	—	t_{Bus}	ns	Time to data active from high-impedance state
9	t_{dis}	Slave MISO disable time	—	t_{Bus}	ns	Hold time to high-impedance state
10	t_v	Data valid (after SPSCK edge)	—	25	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	t_{Bus} - 25	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

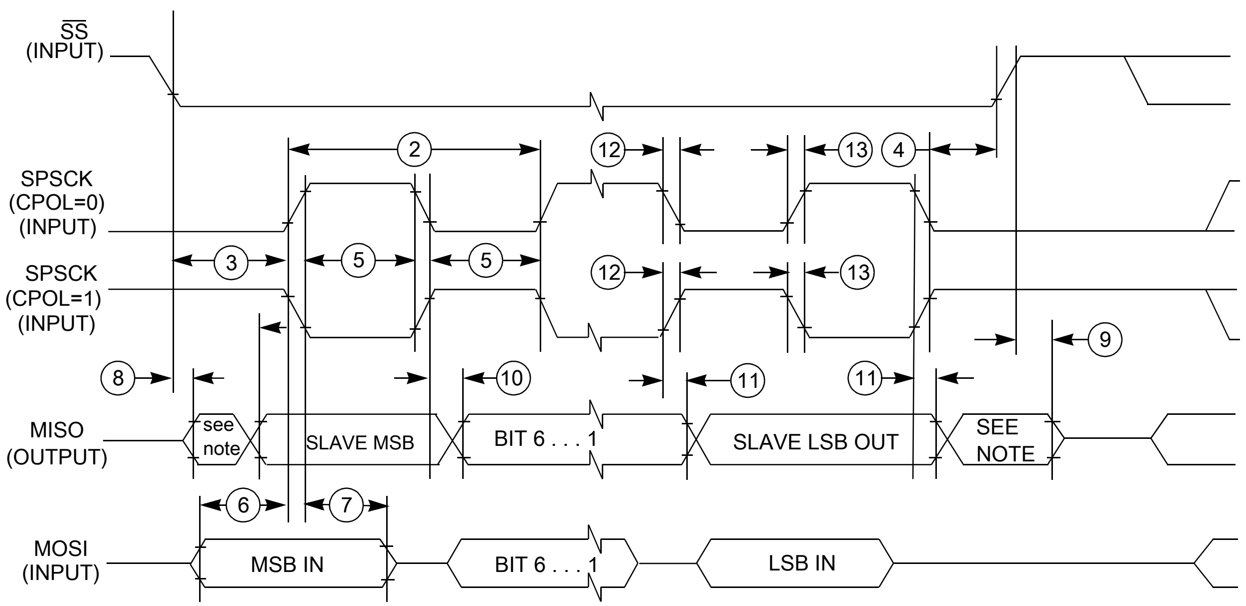


Figure 19. SPI slave mode timing (CPHA = 0)

8 Pinout

8.1 Signal multiplexing and pin assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

Table 19. Pin availability by package pin-count

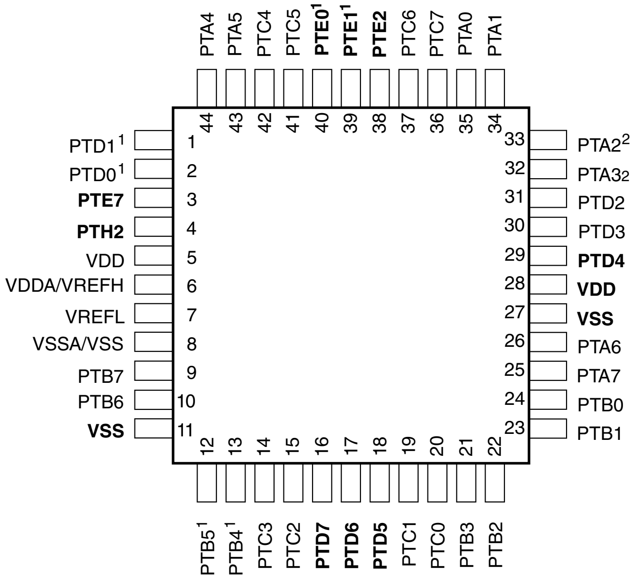
Pin Number			Lowest Priority <-- --> Highest				
64-QFP/ LQFP	**44-LQFP**	**32-LQFP/QFN**	**Port Pin**	**Alt 1**	**Alt 2**	**Alt 3**	**Alt 4**
1	1	1	PTD1[1]	KBI1_P1	FTM2_CH3	SPI1_MOSI	—
2	2	2	PTD0[1]	KBI1_P0	FTM2_CH2	SPI1_SCK	—
3	—	—	PTH7	—	—	—	—
4	—	—	PTH6	—	—	—	—
5	3	—	PTE7	—	FTM2_CLK	—	FTM1_CH1
6	4	—	PTH2	—	BUSOUT	—	FTM1_CH0
7	5	3	—	—	—	—	VDD
8	6	4	—	—	—	VDDA	VREFH[2]
9	7	5	—	—	—	—	VREFL
10	8	6	—	—	—	VSSA	VSS[3]
11	9	7	PTB7	—	I2C0_SCL	—	EXTAL
12	10	8	PTB6	—	I2C0_SDA	—	XTAL
13	11	—	—	—	—	—	VSS
14	—	—	PTH1[1]	—	FTM2_CH1	—	—
15	—	—	PTH0[1]	—	FTM2_CH0	—	—
16	—	—	PTE6	—	—	—	—
17	—	—	PTE5	—	—	—	—
18	12	9	PTB5[1]	FTM2_CH5	SPI0_PCS0	ACMP1_OUT	—
19	13	10	PTB4[1]	FTM2_CH4	SPI0_MISO	$\overline{\text{NMI}}$	ACMP1_IN2
20	14	11	PTC3	FTM2_CH3	—	—	ADC0_SE11
21	15	12	PTC2	FTM2_CH2	—	—	ADC0_SE10
22	16	—	PTD7	KBI1_P7	UART2_TX	—	—
23	17	—	PTD6	KBI1_P6	UART2_RX	—	—
24	18	—	PTD5	KBI1_P5	—	—	—
25	19	13	PTC1	—	FTM2_CH1	—	ADC0_SE9
26	20	14	PTC0	—	FTM2_CH0	—	ADC0_SE8
27	—	—	PTF7	—	—	—	ADC0_SE15

Table continues on the next page...

Table 19. Pin availability by package pin-count (continued)

Pin Number			Lowest Priority <-- --> Highest				
64-QFP/LQFP	44-LQFP	32-LQFP/QFN	Port Pin	Alt 1	Alt 2	Alt 3	Alt 4
28	—	—	PTF6	—	—	—	ADC0_SE14
29	—	—	PTF5	—	—	—	ADC0_SE13
30	—	—	PTF4	—	—	—	ADC0_SE12
31	21	15	PTB3	KBI0_P7	SPI0_MOSI	FTM0_CH1	ADC0_SE7
32	22	16	PTB2	KBI0_P6	SPI0_SCK	FTM0_CH0	ADC0_SE6
33	23	17	PTB1	KBI0_P5	UART0_TX	—	ADC0_SE5
34	24	18	PTB0	KBI0_P4	UART0_RX	—	ADC0_SE4
35	—	—	PTF3	—	—	—	—
36	—	—	PTF2	—	—	—	—
37	25	19	PTA7	—	FTM2_FLT2	ACMP1_IN1	ADC0_SE3
38	26	20	PTA6	—	FTM2_FLT1	ACMP1_IN0	ADC0_SE2
39	—	—	PTE4	—	—	—	—
40	27	—	—	—	—	—	VSS
41	28	—	—	—	—	—	VDD
42	—	—	PTF1	—	—	—	—
43	—	—	PTF0	—	—	—	—
44	29	—	PTD4	KBI1_P4	—	—	—
45	30	21	PTD3	KBI1_P3	SPI1_PCS0	—	—
46	31	22	PTD2	KBI1_P2	SPI1_MISO	—	—
47	32	23	PTA3[4]	KBI0_P3	UART0_TX	I2C0_SCL	—
48	33	24	PTA2[4]	KBI0_P2	UART0_RX	I2C0_SDA	—
49	34	25	PTA1	KBI0_P1	FTM0_CH1	ACMP0_IN1	ADC0_SE1
50	35	26	PTA0	KBI0_P0	FTM0_CH0	ACMP0_IN0	ADC0_SE0
51	36	27	PTC7	—	UART1_TX	—	—
52	37	28	PTC6	—	UART1_RX	—	—
53	—	—	PTE3	—	SPI0_PCS0	—	—
54	38	—	PTE2	—	SPI0_MISO	—	—
55	—	—	PTG3	—	—	—	—
56	—	—	PTG2	—	—	—	—
57	—	—	PTG1	—	—	—	—
58	—	—	PTG0	—	—	—	—
59	39	—	PTE1[1]	—	SPI0_MOSI	—	—
60	40	—	PTE0[1]	—	SPI0_SCK	FTM1_CLK	—
61	41	29	PTC5	—	FTM1_CH1	—	RTCO
62	42	30	PTC4	RTCO	FTM1_CH0	ACMP0_IN2	SWD_CLK
63	43	31	PTA5	IRQ	FTM0_CLK	—	$\overline{\text{RESET}}$
64	44	32	PTA4	—	ACMP0_OUT	—	SWD_DIO

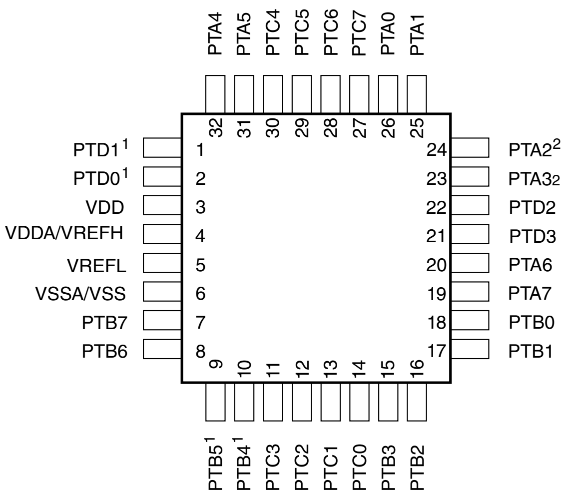
1. This is a high-current drive pin when operated as output.



Pins in **bold** are not available on less pin-count packages.

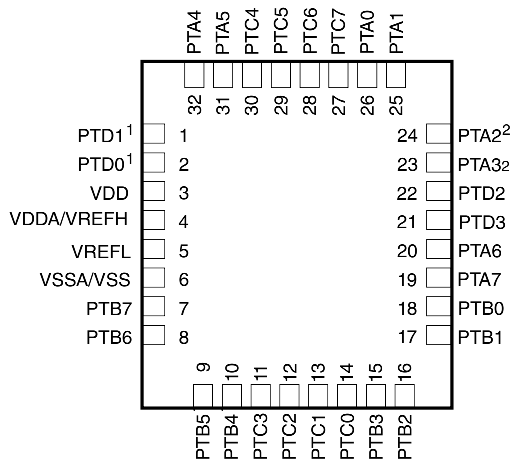
1. High source/sink current pins
2. True open drain pins

Figure 22. 44-pin LQFP package



1. High source/sink current pins
2. True open drain pins

Figure 23. 32-pin LQFP package



1. High source/sink current pins
2. True open drain pins

Figure 24. 32-pin QFN package

9 Revision history

The following table provides a revision history for this document.

Table 20. Revision history

Rev. No.	Date	Substantial Changes
2	3/2014	Initial public release.
3	10/2014	• Added new package of 32-pin QFN information • Updated pin-out • Updated key features of UART, KBI and ADC in the front page • Added a note to the Max. in Supply current characteristics • Updated footnote f_{OSC} = 10 MHz (crystal) in EMC radiated emissions operating behaviors • Added a new section of Thermal operating requirements • Updated NVM specifications • Added reference potential in ADC characteristics • Updated to "All timing assumes high-drive strength is enabled for SPI output pins." in SPI switching specifications
4	07/2016	• Updated the Typical value of E_{TUE} in 12-bit mode and added a note to the 12-bit mode of E_{TUE} and INL in the ADC characteristics.